Dual Nano-power Open Drain Output Comparator

The NCS3402 is a nano-power comparator consuming only 470 nA per channel supply current, which make this device ideal for battery power and wireless handset applications.

The NCS3402 has a minimum operating supply voltage of 2.7 V over the extended industrial temperature range ($T_A = -40^{\circ}$ C to 125°C), while having an input common–mode range of -0.1 to $V_{DD} + 5$ V.

The ultra low supply current makes the NCS3402 an ideal choice for battery powered and portable applications where quiescent current is the primary concern. Reverse battery protection guards the amplifier from an over-current condition due to improper battery installation. For harsh environments, the inputs can be taken 5 V above the positive supply rail without damage to the device.

Features

- Low Supply Current: 470 nA/Per Channel
 - Input Common-Mode Range exceeds the rails
 - \bullet -0.1 V to VDD + 5 V
- Supply Voltage Range: 2.7 V to 16 V
- Reverse Battery Protection Up to 18 V
- Open Drain CMOS Output Stage
- Specified Temperature Range
 - ◆ -40°C to 125°C
- This is a Pb-Free Device

Typical Applications

- Voltage Sense Circuit
- PSU Monitoring Circuit
- Wireless Handsets
- Portable Medical Equipment



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MARKING DIAGRAMS



SOIC-8 D SUFFIX CASE 751



A = Assembly Location

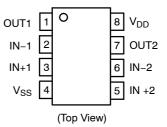
L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

PIN FUNCTION DESCRIPTION

Pin No.	Pin Name	Description
1	OUT1	Channel 1 Output
2	IN-1	Channel 1 Inverting Input
3	IN+2	Channel 2 Non-Inverting Input
4	V _{SS}	Negative Power Supply
5	IN+2	Channel 2 Non-Inverting Input
6	IN-2	Channel 2 Inverting Input
7	OUT2	Channel 2 Output
8	V _{DD}	Positive Power Supply

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	V_{DD}	17	V
Differential Input Voltage	V _{ID}	±20	V
Input Voltage Range (Notes 1 and 2)	V _{IN}	0 to V _{CC} + 5	V
Input Current Range	I _{IN}	±10	mA
Output Current Range	lo	±10	mA
Operating Free-Air Temperature Range	T _A	-40 to +125	°C
Maximum Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{STG}	-65 to 150	°C
Lead Temperature 1.6 mm (1/16 inch) from case for 10 seconds	T _{SLD}	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect

- All voltage values, except differential voltages, are respect to GND
 Input voltage range is limited to 20V or V_{CC} +5 V whichever is smaller

ESD RATINGS

Rating	Symbol	Value	Unit
Human Body Model	HBM	2000	V
Machine Model	MM	200	V

THERMAL CHARACTERISTICS (Note 3)

Rating	Symbol	Value	Unit
Thermal Characteristics Thermal Resistance, Junction-to-Air SOIC8	$R_{ heta JA}$	176	°C/W

^{3.} Power dissipation must be considered to ensure the maximum junction temperature (θ_{JA}) is not exceeded.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Min	Max	Unit
Supply voltage	V _{DD}	Single supply	2.7	16	V
		Split supply	±1.35	±8	
Common-mode input voltage range	V _{ICR}		-0.1	V _{DD} +5	V
Operating free-air temperature	T _A		- 40	125	°C

DC PERFORMANCE ELECTRICAL CHARACTERISTICS AT SPECIFIED OPERATING FREE-AIR TEMPERATURE, $V_S = 2.7 \text{ V}$, 5 V, 15 V (unless otherwise noted)

Parameter	Symbol	Testing Conditions	T _A	Min	Тур	Max	Unit
			25°C		250	3600	
Input offset voltage	V _{IO}	$V_{CM} = V_S/2$, $R_S = 50 \Omega$, $R_P = 1 M\Omega$	Full range			4400	μV
Offset voltage drift	ΔV_{IO}		25°C		3		μV/°C
			25°C	55	72		
		V_{CM} = 0 to 2.7 V, R_S = 50 Ω	Full range	50			
Common mode rejection		CMRR $V_{CM} = 0$ to 5 V, $R_S = 50 \Omega$	25°C	60	76		
Common-mode rejection ratio	CMRR		Full range	55			dB
			25°C	65	88		
		V_{CM} = 0 to 15 V, R_S = 50 Ω	Full range	60			
Large-signal differential voltage amplification	A _{VD}	R_P = 1 $M\Omega$	25°C		1000		V/mV

INPUT/OUTPUT CHARACTERISTICS SPECIFIED OPERATING FREE-AIR TEMPERATURE,

 $V_S = 2.7 \text{ V}, 5 \text{ V}, 15 \text{ V} \text{ (unless otherwise noted)}$

Input offset current			25°C	20	100	
(Note 4)	I _{IO}	V V/0 D 1 MO D 50 O	Full range		1000	pА
Input bias current		$V_{CM} = V_S/2$, $R_P = 1 M\Omega$, $R_S = 50 \Omega$	25°C	80	250	
(Note 4)	I _{IB}	I _{IB}			3000	pА
Differential input resistance	R _{ID}	V _{in} = V _S /2	25°C	300		МΩ
High-impedance output leakage current	l _{oz}	$V_{CM} = V_S/2, V_O = V_{CC}, V_{ID} = 1 V$	25°C	50		pА
		$V_{CM} = V_S/2$, $I_{OL} = 2 \mu A$, $V_{ID} = -1 V$	25°C	8		
Low-level output voltage	out voltage V _{OL}	$V_{CM} = V_S/2$, $I_{OL} = 50 \mu A$, $V_{ID} = -1 V$	25°C	80	200	mV
			Full range		300	

POWER SUPPLY SPECIFIED OPERATING FREE-AIR TEMPERATURE, V_{CC} = 2.7 V, 5 V, 15 V (unless otherwise noted)

				25°C		470	550	
Supply current (per channel)			Output state low	Full range			750	A
	Icc	R _P = No pullup		25°C		560	640	nA
		Output state high	Full range			950		
Power supply rejection ratio			V_{CC} = 2.7 V to 5 V $V_{S/2}$, No pad V_{CC} = 5 V to 15 V	25°C	75	100		
	PSRR	V _{CM} = V _S /2, No		Full range	70			dB
	PSHR load	load		25°C	85	105		uБ
				Full range	80			

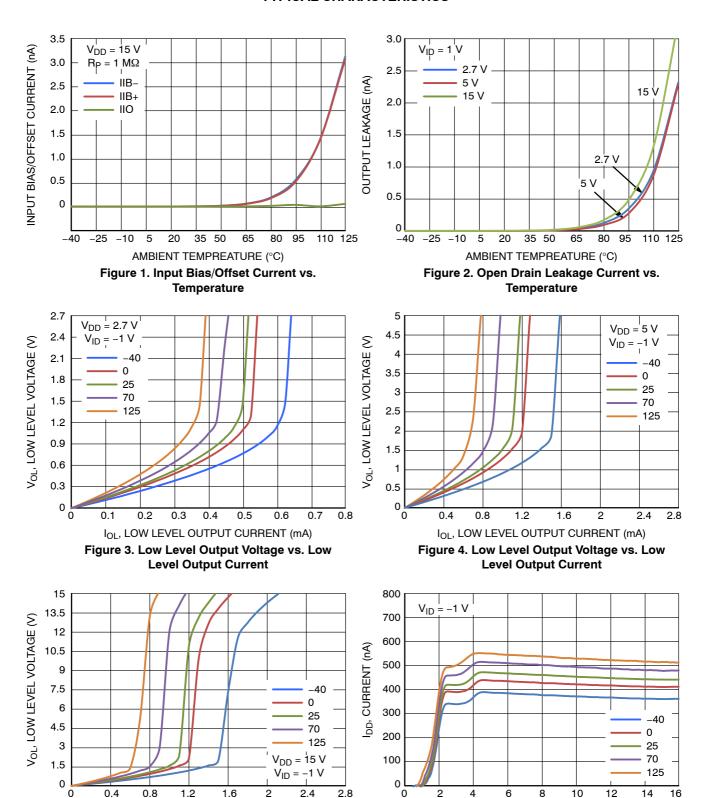
^{4.} Guaranteed by design or characterization.

SWITCHING CHARACTERISTICS AT RECOMMENDED OPERATING CONDITIONS,

 V_{CC} = 2.7 V, 5 V, 15 V, T_A = 25°C (unless otherwise noted)

Parameter	Symbol	Testing Conditions		T _A	Min	Тур	Max	Unit
Propagation delay time, low-to-high-level			Overdrive = 2 mV			220		
	t _(PLH)		Overdrive = 10 mV	25°C		85		
		f = 10 kHz, VSTEP = 100 mV,	Overdrive = 50 mV			30		
		$R_P = 1 M\Omega$, $C_1 = 10 pF$	Overdrive = 2 mV			250		μS
Propagation delay time, high-to-low-level output	t _(PHL)	οι - 10 μι	Overdrive = 10 mV	25°C		55		
g			Overdrive = 50 mV			18		
Fall time	tf	R _P = 1 MΩ	2, C _L = 10 pF	25°C		5		μs

TYPICAL CHARACTERISTICS



I_{OL}, LOW LEVEL OUTPUT CURRENT (mA)

Figure 5. Low Level Output Voltage vs. Low
Level Output Current

 $\label{eq:VDD} V_{DD} \mbox{ SUPPLY (V)}$ Figure 6. I_{DD} vs. V_{DD} vs. Temperature

TYPICAL CHARACTERISTICS

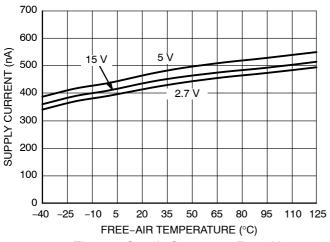


Figure 7. Supply Current vs. Free-Air **Temperature**

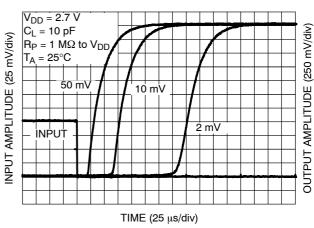


Figure 8. Propagation Delay L-H (2.7 V)

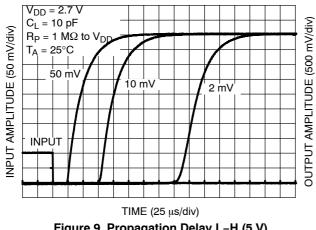


Figure 9. Propagation Delay L-H (5 V)

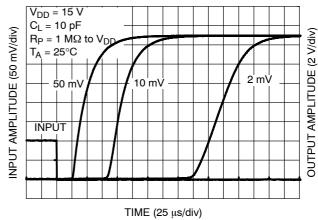


Figure 10. Propagation Delay L-H (15 V)

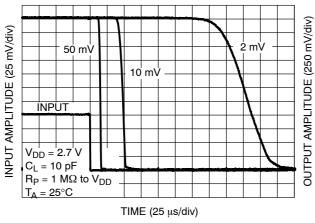


Figure 11. Propagation Delay H-L (2.7 V)

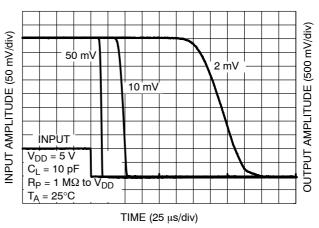


Figure 12. Propagation Delay H-L (5 V)

TYPICAL CHARACTERISTICS

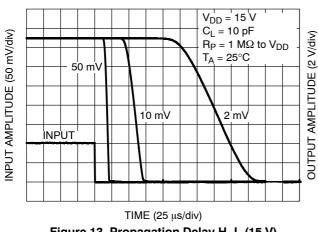


Figure 13. Propagation Delay H-L (15 V)

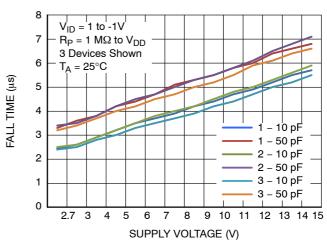


Figure 14. Output Fall Time vs. Power Supply

ORDERING INFORMATION

Device	Package	Shipping [†]
NCS3402DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SOIC-8 NB CASE 751-07 **ISSUE AK**

DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

= Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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STYLE 4: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 2 4. ANODE 5. ANODE #2 6. ANODE #2 7. ANODE #1 8. COMMON CATHODE
STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 STAGE Vd 7. EMITTER, #1 AGE Vd 8. COLLECTOR, #1
STYLE 12: 1 PIN 1. SOURCE 2 SOURCE 2 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COMMON 6. COLLECTOR, DIE #2 6. COMMON 7. COLLECTOR, DIE #1 6. COMMON 8. COLLECTOR, DIE #1
STYLE 20: 1 PIN 1. SOURCE (N) 2. GATE (N) 2 3. SOURCE (P) 4. GATE (P) 5. DRAIN 2 6. DRAIN 7. DRAIN 1 8. DRAIN
STYLE 24: PIN 1. BASE N ANODE/GND 2. EMITTER N ANODE/GND 3. COLLECTOR/ANODE UT 5. CATHODE N ANODE/GND 6. CATHODE N ANODE/GND 7. COLLECTOR/ANODE UT 8. COLLECTOR/ANODE
STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND E 5. V_MON E 6. VBULK E 7. VBULK 8. VIN

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